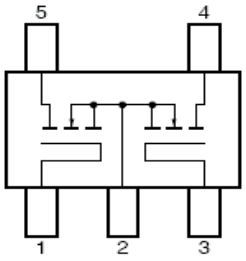
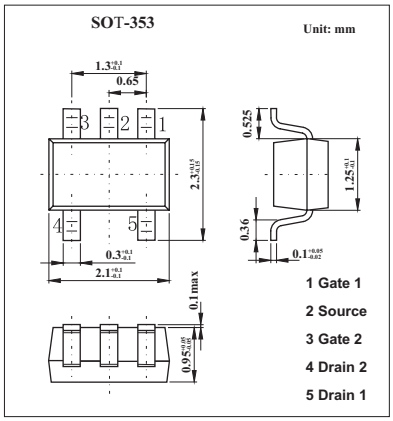
MOS Field Effect Transist

UPA572T

Features

- Two source common MOS FET circuits
- Directly driven by 3 V power supply
- Automatic mounting supported





Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to Source Voltage (VGS = 0)	VDSS	30	V
Gate to Source Voltage (VDS = 0)	VGSS	±7	V
Drain Current (DC)	ID(DC)	±100	mA
Drain Current (pulse) *	ID(pulse)	±200	mA
Total Power Dissipation	PT	200 (Total)	mW
Channel Temperature	Tch	150	℃
Operating Temperature	Topt	-55 to +80	℃
Storage Temperature	Tstg	-55 to +150	℃

* PW ⩽ 10 ms, Duty Cycle ⩽ 50 %

Electrical Characteristics Ta = 25℃

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	IDSS	VDS = 30 V, VGS = 0			1.0	μA
Gate Leakage Current	IGSS	VGS =± 5 V, VDS = 0			±3.0	μA
Gate Cut-off Voltage	VGS(off)	VDS = 3 V, ID = 10 μA	0.8	1.0	1.5	V
Forward Transfer Admittance	|yfs|	VDS = 3 V, ID = 10 mA	20	50		mS
Drain to Source On-State Resistance	RDS(on)1	VGS = 2.5 V, ID = 1 mA		7	13	Ω
Drain to Source On-State Resistance	RDS(on)2	VGS = 4.0 V, ID = 10 mA		5	8	Ω
Input Capacitance	Ciss	VDS = 5.0 V, VGS = 0, f = 1 MHz		16		pF
Output Capacitance	Coss			14		pF
Reverse Transfer Capacitance	Crss			2		pF
Turn-On Delay Time	td(on)	VDD = 5 V, ID = 10 mA, VGS(on) = 5 V, RG = 10 Ω, RL = 500 Ω		15		ns
Rise Time	tr			20		ns
Turn-Off Delay Time	td(off)			100		ns
Fall Time	tf			100		ns

Marking

Marking	DB